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IN THE CLAIMS:

Please cancel claims 44-46, without prejudice or disclaimer.

Please substitute the following amended claims for the corresponding original claims. A marked copy of the claim amendments is attached hereto.

18. (amended three times) A method of etching a substrate in a chamber and cleaning etchant residue from surfaces in the chamber, the method comprising the steps of:

- (a) electrostatically holding the substrate in the chamber;
- (b) providing an energized first gas in the chamber, the energized first gas being capable of etching a first material on the substrate thereby depositing a first etchant residue on the surfaces in the chamber;
- (c) after (b), providing an energized second gas comprising a fluorinated cleaning gas in the chamber, the energized second gas being capable of etching a second material on the substrate while suppressing deposition of a second etchant residue onto the first etchant residue, the first etchant residue being compositionally different from the second etchant residue; and
- (d) after (c), providing a cleaning gas comprising an oxygen containing gas in the chamber and coupling RF power to energize the cleaning gas to clean the first and second etchant residue deposits formed on the surfaces in the chamber and simultaneously remove residual charge accumulated in the substrate.

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30 41. (amended three times) A method of cleaning a chamber to remove residue from surfaces of a ceiling portion in the chamber, the chamber having an antenna adjacent to the ceiling portion, and the method comprising the steps of:

- (a) providing an energized first process gas in the chamber to clean the surfaces in the chamber, the first process gas consisting essentially of oxygen; and
- (b) setting a chamber source power level applied to the antenna to remove residue from the surfaces of the ceiling portion.

30 51. (amended three times) A method of etching a substrate in a chamber and at least partially removing etchant residue from surfaces in the chamber, the method comprising:

- (a) electrostatically holding the substrate in the chamber, the substrate having a first and a second layer thereon, the second layer comprising a metal silicide layer;
- (b) providing a first energized gas in the chamber to etch the first layer;
- (c) providing a second energized gas in the chamber to etch the second layer and at least partially remove the etchant residue formed on the surfaces in the chamber in (b); and
- (d) providing an energized cleaning gas to at least partially remove residues formed on surfaces in the chamber in (b) and (c) and simultaneously remove residual charge accumulated in the substrate.

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Please add the following new claims:

~~18~~ 55. (new) A method according to claim ~~18~~¹³ wherein the substrate comprises a metal silicide layer, and wherein (c) comprises providing the energized second gas comprising the fluorinated cleaning gas to etch the metal silicide layer.

~~32~~ 56. (new) A method according to claim ~~41~~³⁰ wherein (b) comprises setting a chamber source power level applied to the antenna of about 500 Watts.

~~44~~ 57. (new) A method according to claim ~~51~~³⁴ wherein (c) comprises providing a second energized gas comprising a fluorinated gas.

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